

0.65W, 5kV_{RMS} Complete Isolated DC-DC Converter

1 Features

• Complete Switch Mode Power Supply

- High integration with internal transformer
- Soft-start reduces input inrush current and output overshoot
- Overload and short-circuit protection
- Thermal shutdown
- 4.5 V to 5.5 V Input Voltage Range
- Selectable Output voltages
- 3.3V, 3.7V, 5V and 5.4V output options
- Delivers up to 650mW(5V/130mA) Output Power
- Robust Galvanic Isolation Barrier
- High lifetime: > 40 years
- Up to 5000 V_{RMS} isolation rating
- ±150 kV/μs typical CMTI
- Wide Operating Temperature Range: -40°C to 125°C
- Low Profile SOIC16-WB (10.30mm × 7.50) Package
- Safety-Related Certifications (Pending)
- 5kV_{RMS} isolation for 1 minute per UL 1577
- 7071V_{PK} V_{IOTM} and 849V_{PK} V_{IORM} reinforced isolation per DIN V VDE V 0884-11:2017-01
- IEC 60950 \ IEC 60601 and EN 61010 certifications per CQC, TUV and CSA

2 Applications

- Instruments and Apparatuses
- Industrial automation
- Motor Control
- Medical Equipment
- Industrial Sensors
- Telecom Equipment

3 General Description

The CA-IS3105W is a complete isolated DC-DC converter with up to $5kV_{RMS}$ isolation rating. This device integrates most of the components needed for an isolated power supply —switching controller, power switches, transformer, soft-start, protection circuit etc. — into a single, compact SOIC package. The result is an efficient and compact fully integrated solution that is easy to comply with EMI requirements and makes power-supply design as easy as

possible. Operating over an input voltage range of 4.5V to 5.5V, the CA-IS3105W provides a fixed output voltage of 3.3V, 3.7V, 5V or 5.4V set by pin SEL. Only output, input bypass capacitors, and a pull-up resistor for 3.7V or 5.4V outputs are needed to finish the design.

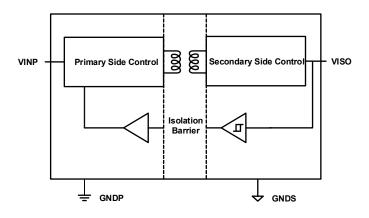
The CA-IS3105W device features a unique control scheme, which can quickly respond to load transient and accurately regulate the output voltage. The device is capable of delivering a load up to 650mW output power and offering soft-start, current limit, short-circuit protection and thermal shutdown protection features to better enhance the reliability of the system. The CA-IS3105W includes an enable input pin (EN). Connect the EN pin to the VINP input voltage or force this pin high to turn on the DC-DC converter. Force this pin low to disable the device and enter shutdown mode. In shutdown mode, the device stops switching operation with microampere standby supply current.

The CA-IS3105W is available in wide-body SOIC16 package and operates over -40°C to +125°C temperature range.

Device Information

Part number	Package	Package size (NOM)
CA-IS3105W	SOIC16-WB(W)	10.30 mm × 7.50 mm

Simplified Block Diagram





4 Ordering Information

Table 4-1. Ordering Information

Part #	Input Voltage	Output Voltage	Output Power	Package
CA-IS3105W	4.5V to 5.5V	3.3V, 3.7V, 5V, 5.4V	650mW	SOIC16-WB(W)



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5 Revision history

Revision Number	Description	Revised date	Page Changed
Version 1.00	N/A		N/A
Version 1.01	Update the POD , update the tape reel information	2022.12.19	16, 18
Version 1.02	Update SEL Pin description for Viso setting	2023.09.18	7

6 Pin Configuration and Description

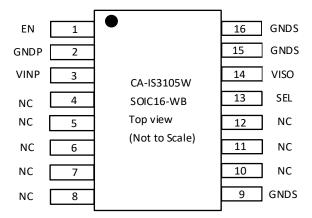


Figure 6-1. CA-IS3105W Top View

Table 6-1. CA-IS3105W Pin Description

Pin name	Pin number	Туре	Description
EN	1	Input	Enable input, active-high. Force this pin high to enable the device. Force this
,		pat	pin low to disable the device and put the device into shutdown mode.
GNDP	2	GND	Primary side local ground.
VINP	3	Power	Primary side supply input. Bypass VINP to GNDP with both 0.1μF and 10μF
VIINE	3	rowei	capacitors as close to the device as possible.
NC¹	4, 5, 6, 7, 8		No internal connection. These pins belong to primary side voltage domain.
INC	4, 3, 6, 7, 8	-	Connect them to GNDP externally.
GNDS 9, 15, 16		GND	Secondary side ground return connection for V _{ISO} .
NC ¹	10 11 12		No internal connection. These pins belong to isolated voltage domain.
NC-	10, 11, 12	-	Connect them to GNDS externally.
			Output voltage V _{ISO} select pin:
			V _{ISO} = 5.0 V when SEL is shorted to VISO;
SEL	13	lanut	V_{ISO} = 5.4 V when SEL is connected to VISO through a 100k Ω resistor;
SEL	13	Input	V _{ISO} = 3.3 V when SEL is shorted to GNDS;
			V_{ISO} = 3.7V when SEL is connected to GNDS through a 100k Ω resistor.
			Don't leave this pin open.
VISO	1.4	Dower	Isolated supply voltage pin. Bypass VISO to GNDS with both 0.1μF and 10μF
VISO	14	Power	capacitors as close to the device as possible.

Note:

^{1.} These pins do not have internal connection. We recommend to connect them to the corresponding ground plane to improve the PCB heat dissipation.



Specifications

Absolute Maximum Ratings^{1, 2} 7.1

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	Parameters	Minimum value	Maximum value	Unit
V _{INP}	Power supply voltage	-0.5	6.0	V
V _{ISO}	Isolated supply voltage	-0.5	6.0	V
EN	EN input voltage	-0.5	V _{INP} +0.3 ³	V
SEL	SEL input voltage	-0.5	V _{ISO} +0.3	V
Tj	Junction temperature	-40	150	°C
T _{STG}	Storage temperature range	-65	150	°C

Notes:

- The stresses listed under "Absolute Maximum Ratings" are stress ratings only, not for functional operation condition. Exposure to absolute 1. maximum rating conditions for extended periods may cause permanent damage to the device.
- 2. All voltage values are with respect to the local ground (GNDP or GNDS) and are peak voltage values.
- Maximum voltage must not be exceed 6 V. 3.

ESD Ratings 7.2

		Value	Unit
V _{ESD} Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins ¹	±3000	V
	Charged device model (CDM), per JEDEC Specification JESD22-C101, all pins ²	±2000	V
Notos	later.		

- Per JEDEC document JEP155, 500V HBM allows safe manufacturing of standard ESD control process.
- Per JEDEC document JEP157, 250V CDM allows safe manufacturing of standard ESD control process.

7.3 **Recommended Operating Conditions**

	Parameters	Minimum	Typical	Maximum	Unit
		value	value	value	
V_{INP}	Power supply voltage	4.5	5	5.5	V
V_{EN}	EN input voltage	0		5.5	V
V _{ISO}	Isolated supply voltage	0		5.7	V
V_{SEL}	SEL input voltage	0		5.7	V
T _A	Ambient Temperature	-40		125	°C
T _J	Junction temperature	-40		150	°C

Thermal Information 7.4

Thermal Metric	CA-IS3105W	Unit
Heilidi Wetric	SOIC16-WB(W)	Ollit
R _{BJA} Junction-to-ambient thermal resistance	73.8	°C/W

7.5 **Power Ratings**

Parameters	Test Conditions	Minimum value	Typical value	Maximum value	Unit
P _D Power dissipation	V _{INP} = 5.5V, V _{ISO} = 5.4V, 130mA output current		1.27W	1.4	W



7.6 Insulation Specifications

7.5	Parameters	Test Conditions	Specifications W	Unit
CLR	External clearance	Shortest terminal-to-terminal distance through air	- W - 8	mm
CPG	External creepage	Shortest terminal-to-terminal distance across the package surface	8	mm
DTI	Distance through the insulation	Minimum internal gap (internal clearance)	21	μm
CTI	Comparative tracking index	DIN EN 60112 (VDE 0303-11); IEC 60112	>400	V
	Material group	According to IEC 60664-1	I	
		Rated mains voltage ≤ 300 V _{RMS}	I-IV	
DIN V \	IEC 60664-1 over-voltage category	Rated mains voltage ≤ 400 V _{RMS}	I-IV	1
		Rated mains voltage ≤ 600 V _{RMS}	1-111	1
DIN V V	/DE V 0884-11:2017-01 ¹	-	1	
V _{IORM}	Maximum repetitive peak isolation voltage	AC voltage (bipolar)	849	V_{PK}
V _{IOWM}	Maximum operating isolation voltage	AC voltage; time-dependent dielectric breakdown (TDDB) test	600	V _{RMS}
	, ,	DC voltage	849	V _{DC}
V _{IOTM}	Maximum transient isolation voltage	$V_{TEST} = V_{IOTM}$, t=60 s (qualification); $V_{TEST} = 1.2 \times V_{IOTM}$, t=1 s (100% product test)	7070	V _{PK}
V _{IOSM}	Maximum surge isolation voltage ²	Test method per IEC 60065, 1.2/50 μ s waveform, $V_{TEST} = 1.6 \times V_{IOSM}$ (production test)	6250	V _{PK}
q_{pd}	Apparent charge ³	Method a, after input/output safety tests subgroup 2/3, $V_{ini} = V_{IOTM}, t_{ini} = 60s; \\ V_{pd(m)} = 1.2 \times V_{IORM}, t_m = 10s \\ Method a, after environmental tests subgroup 1, \\ V_{ini} = V_{IOTM}, t_{ini} = 60s;$	≤5 ≤5	pC
		$\begin{split} &V_{pd(m)} = 1.6 \times V_{IORM}, t_m = 10s \\ &\text{Method b1, at routine test (100\% production test) and} \\ &\text{preconditioning (sample test)} \\ &V_{ini} = 1.2 \times V_{IOTM}, t_{ini} = 1s; \\ &V_{pd(m)} = 1.875 \times V_{IORM}, t_m = 1s \end{split}$	≤5	
C _{IO}	Barrier capacitance, input to output ⁴	$V_{10} = 0.4 \times \sin(2\pi ft)$, f = 1 MHz	3.5	pF
		V _{IO} = 500 V, T _A = 25°C	>1012	
R _{IO}	Isolation resistance , input to output ⁴	V _{IO} = 500 V, 100°C ≤ T _A ≤ 125°C	>1011	Ω
		V _{IO} = 500 V at T _S = 150°C	>109	
	Pollution degree		2	
UL 157	7			
V _{ISO}	Maximum isolation voltage	$V_{TEST} = V_{ISO}$, t = 60 s (certified) $V_{TEST} = 1.2 \times V_{ISO}$, t = 1 s (100% production test)	5000	V _{RM}
		:	•	

Notes:

- 1. This coupler is suitable for "safe electrical insulation" only within the safety ratings. Compliance with the safety ratings shall be ensured by means of suitable protective circuits.
- 2. Devices are immersed in oil during surge characterization.
- 3. The characterization charge is discharging charge (pd) caused by partial discharge.
- 4. Capacitance and resistance are measured with all pins on field-side and logic-side tied together.

7.7 Safety-Related Certifications

VDE (pending)	UL (pending)	CQC (pending)	TUV (pending)				
Certified according to	Certified according to	Certified according to GB4943.1-	Certified according to EN61010-1:2010 (3rd				
DIN V VDE V 0884-	UL 1577 Component	20111	Ed) and EN60950-1:2006/A2:2013				
11:2017-01	Recognition Program						



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7.8 **Electrical Characteristics**

Over operating temperature range $T_A = -40$ to 125°C, $V_{INP} = 4.5$ V to 5.5V, SEL connected to V_{ISO} , $C_{VINP} = C_{VISO} = 10$ µF, unless otherwise specified. All typical specs are at $T_A = 25$ °C and $V_{INP} = 5V$.

Now_O_D V_Now quiescent current Figure 7-28 EN = HIGH, SEL connected to V _{So} (5V output), see Figure 7-28 EN = HIGH, SEL connected to GNDS (3.3V output) 7.3 20 r.		Parameters	Test Conditions	Minimum value	ТҮР	Maximum value	Unit		
No.	Power Sup	ply Input							
Figure 7- 28	I _{VINP_SD}	V _{INP} shutdown current	EN = LOW, see Figure 7- 27		0.05	10	μΑ		
			EN = HIGH, SEL connected to V _{ISO} (5V output), see		0.4	20	mΛ		
		V suissant summent	Figure 7- 28		0.4	20	mA		
EN = HIGH, SEL connected to GNDS (3.3V output) 7.3 2.0 n	I _{VINP} O	•	EN = HIGH, SEL $100k\Omega$ to VISO (5.4Voutput)		8.8	20	mA		
None Section None		1 _{OUT} = 0% 10au	EN = HIGH, SEL connected to GNDS (3.3V output)		7.3	20	mA		
Vivido			EN = HIGH, SEL $100k\Omega$ to GNDS (3.7V output)		7.5	20	mA		
Volume	I _{VINP_SC}	• • •	VISO short to GNDS		42	100	mA		
Threshold Common-mode transient immunity Sew Rate of GNDP versus GNDS, Vox et all post of the page of the pa	$V_{\text{UVLO+}}$				2.6	3.0	V		
Post	V _{UVLO-}			2.1	2.3		V		
$ V_{\text{NL},EN} $	V _{HYS(UVLO)}	,			0.3	0.6	V		
VILO Line regulation VISO Line regulation Line regulati	EN, SEL pin	s		·			ı		
VILEQUENCE VISO Line regulation SEL short to GNDS (3.3V output), Iso = 50mA, VINP = 4.5V to 5.5 V, see Figure 7 - 23 VISO Line regulation Line regulation SEL short to GNDS (3.3V output), Iso = 0 to 130mA, see Figure 7 - 19 VISO Line regulation SEL short to GNDS (3.3V output), Iso = 0 to 130mA, see Figure 7 - 19 VISO Load regulation SEL short to GNDS (3.3V output), Iso = 0 to 130mA, see Figure 7 - 19 VISO COMMON SEL short to GNDS (3.3V output), Iso = 50mA, VINP = 4.5V to 5.5V, see Figure 7 - 20 VISO COMMON SEL short to GNDS (3.3V output), Iso = 50mA, VINP = 4.5V to 5.5V, see Figure 7 - 20 VISO COMMON SEL short to GNDS (3.3V output), Iso = 50mA, VINP = 4.5V to 5.5V, see Figure 7 - 21 VISO COMMON SEL short to GNDS (3.3V output), Iso = 50mA, VINP = 4.5V to 5.5V, see Figure 7 - 23 VISO COMMON SEL short to GNDS (3.3V output), Iso = 50mA, VINP = 4.5V to 5.5V, see Figure 7 - 23 VISO COMMON SEL short to GNDS (3.3V output), Iso = 0 to 130mA, see Figure 7 - 17 VISO COMMON SEL short to GNDS (3.3V output), Iso = 0 to 130mA, see Figure 7 - 19 VISO COMMON SEL short to GNDS (3.3V output), Iso = 0 to 130mA, See Figure 7 - 20 VISO COMMON SEL short to GNDS (3.3V output), Iso = 0 to 130mA, See Figure 7 - 20 VISO COMMON SEL short to GNDS (3.3V output), Iso = 0 to 130mA, See Figure 7 - 25 VISO COMMON SEL short to GNDS (3.3V output), Iso = 0 to 130mA, See Figure 7 - 25 VISO COMMON SEL short to GNDS (3.3V output), Iso = 0 to 130mA, See Figure 7 - 25 VISO COMMON SEL short to GNDS (3.3V output), Iso = 0 to 130mA, See Figure 7 - 25 VISO COMMON SEL short to GNDS (3.3V output), Iso = 0 to 130mA, See Figure 7 - 25 VISO COMMON SEL short to GNDS (3.3V output), Iso = 0 to 130mA, See Figure 7 - 25 VISO COMMON SEL short to GNDS (3.3V output), Iso = 0 to 130mA, See Figure 7 - 25 VISO COMMON SEL Short to GNDS (3.3V output), Iso = 0 to 130mA, See Figure 7 - 25 VISO COMMON	V _{IH_EN}	EN Input threshold, logic HIGH		2			V		
Input leakage current V _{INP} = 5V, V _{EN} = 5V 5 20 1 Isolated DC-DC Converter		EN Input threshold, logic LOW				0.8	V		
SEL connected to V _{ISO} (SV output), I _{ISO} = 50mA 4.65 5.0 5.35		Input leakage current	$V_{INP} = 5V$, $V_{EN} = 5V$		5	20	μΑ		
VISO Isolated output voltage SEL 100KΩ to VISO (5.4V output), I _{ISO} = 50mA 5.02 5.4 5.78	Isolated DO	C-DC Converter		•			•		
Viso Isolated output voltage SEL connected to GNDS (3.3V output), I _{Iso} = 50mA 3.07 3.3 3.53			SEL connected to V _{ISO} (5V output), I _{ISO} = 50mA	4.65	5.0	5.35			
SEL connected to GNDS (3.3V output), I _{ISO} = 50mA 3.07 3.3 3.53	V	Isolated output voltage	SEL 100KΩ to VISO (5.4V output), I_{ISO} = 50mA	5.02	5.4	5.78	V		
VISO	VISO	Isolated output voltage	SEL connected to GNDS (3.3V output), I _{ISO} = 50mA	3.07	3.3	3.53			
VISO (RIP) Voltage ripple on isolated supply output (pk-pk) I _{ISO} = 100mA, see Figure 7- 9 20MHz bandwidth, SEL short to GNDS (3.3V output), I _{ISO} = 100mA, see Figure 7- 11 55 100 100			SEL 100KΩ to GNDS (3.7V output), I_{ISO} = 50mA	3.44	3.7	3.96	1		
VISO _(RIP) output (pk-pk) Voltage ripple on isolated supply output (pk-pk) I _{ISO} = 100mA, see Figure 7- 9 20MHz bandwidth, SEL short to GNDS (3.3V output), I _{ISO} = 50mA, V _{INP} = 4.5V to 5.5 V, see Figure 7- 21 55 100 VISO _(LINE) Line regulation Line regulation SEL short to VISO (5V output), I _{ISO} = 50mA, V _{INP} = 4.5V to 5.5 V, see Figure 7- 21 2 5 VISO _(LOAD) Load regulation SEL short to GNDS (3.3V output), I _{ISO} = 0 to 130mA, see Figure 7- 23 1% 2% SEL short to VISO (5V output), I _{ISO} = 0 to 130mA, see Figure 7- 17 1% 2% SEL short to GNDS (3.3V output), I _{ISO} = 0 to 130mA, see Figure 7- 19 1% 2% EFF Efficiency@maximum load current I _{ISO} = 130 mA, C _{LOAD} = 0.1µF 10µF; V _{ISO} =5V, see Figure 7- 25, Figure 7- 26 55% 55% CMTI Common-mode transient immunity Slew Rate of GNDP versus GNDS, V _{CM} =1200V _{RMS} ±100 ±150 kV Versignle voltage (neak to neak) 10% to 90% load step with 5A/us slew-rate; see 80 100 no			20MHz bandwidth, SEL short to VISO (5V output),		65	100			
VISO _(LINE) Line regulation SEL short to GNDS (3.3V output),	$VISO_{(RIP)}$	Voltage ripple on isolated supply	I _{ISO} = 100mA, see Figure 7- 9		03	100	mV		
$ \begin{array}{c} \text{VISO}_{(\text{LINE})} & \text{Line regulation} \\ & \begin{array}{c} \text{V}_{\text{INP}} = 4.5 \text{V to } 5.5 \text{ V, see Figure 7- 21} \\ \text{SEL short to GNDS (3.3 V output), I}_{\text{ISO}} = 50 \text{mA}, \\ \text{V}_{\text{INP}} = 4.5 \text{V to } 5.5 \text{V, see Figure 7- 23} \\ \\ \text{VISO}_{(\text{LOAD})} & \begin{array}{c} \text{Load regulation} \\ \end{array} \end{array} \begin{array}{c} \text{SEL short to VISO (5V output), I}_{\text{ISO}} = 0 \text{ to } 130 \text{mA, see} \\ \text{Figure 7- 17} \\ \\ \text{SEL short to GNDS (3.3 V output), I}_{\text{ISO}} = 0 \text{ to } 130 \text{mA, see} \\ \text{Figure 7- 19} \\ \\ \text{I}_{\text{ISO}} = 130 \text{ mA, C}_{\text{LOAD}} = 0.1 \mu \text{F} \mid 10 \mu \text{F; V}_{\text{ISO}} = 5 \text{V, see} \\ \text{Figure 7- 25, Figure 7- 26} \\ \\ \text{I}_{\text{ISO}} = 130 \text{mA, C}_{\text{LOAD}} = 0.1 \mu \text{F} \mid 10 \mu \text{F; V}_{\text{ISO}} = 3.3 \text{V, see} \\ \text{Figure 7- 25, Figure 7- 26} \\ \\ \text{CMTI} & \text{Common-mode transient immunity} & \text{Slew Rate of GNDP versus GNDS, V}_{\text{CM}} = 1200 \text{V}_{\text{RMS}} \\ \\ \text{10% to 90% load step with 5A/us slew-rate; see} \\ \end{array} \begin{array}{c} 2 \\ \text{5} \\ \text{100} \\ 1$		output (pk-pk)	, , ,		55	100	1111		
VISO _(LOAD) Load regulation			, , , , , , , , , , , , , , , , , , , ,		2	5			
VISO _(LOAD) Load regulation SEL short to VISO (5V output), $I_{ISO} = 0$ to 130mA, see Figure 7- 17 SEL short to GNDS (3.3V output), $I_{ISO} = 0$ to 130mA, see Figure 7- 19 $I_{ISO} = 130 \text{ mA}, C_{LOAD} = 0.1 \mu \text{F} \mid \mid 10 \mu \text{F}; V_{ISO} = 5\text{V}, \text{ see}$ Figure 7- 25, Figure 7- 26 $I_{ISO} = 130 \text{ mA}, C_{LOAD} = 0.1 \mu \text{F} \mid \mid 10 \mu \text{F}; V_{ISO} = 3.3\text{V}, \text{ see}$ Figure 7- 25, Figure 7- 26 CMTI Common-mode transient immunity Slew Rate of GNDP versus GNDS, $V_{CM} = 1200 V_{RMS}$ 10% to 90% load step with 5A/us slew-rate; see	VISO _(LINE)	Line regulation	1		2	5	mV/V		
VISO _(LOAD) Load regulation			SEL short to VISO (5V output), I _{ISO} = 0 to 130mA, see		1%	2%			
$EFF \qquad Efficiency@maximum load current \\ \hline EFF \qquad Efficiency@maximum load current \\ \hline I_{ISO} = 130 mA, C_{LOAD} = 0.1 \mu F \mid\mid 10 \mu F; V_{ISO} = 5 V, see \\ \hline Figure 7- 25, Figure 7- 26 \\ \hline I_{ISO} = 130 mA, C_{LOAD} = 0.1 \mu F \mid\mid 10 \mu F; V_{ISO} = 3.3 V, see \\ \hline Figure 7- 25, Figure 7- 26 \\ \hline CMTI \qquad Common-mode transient immunity \qquad Slew Rate of GNDP versus GNDS, V_{CM} = 1200 V_{RMS} \\ \hline V_{ISO} = 1200 V_{RMS} \qquad \pm 100 \qquad \pm 150 \qquad kV_{CM} = 100 V_{RMS} \\ \hline V_{ISO} = 130 mA, C_{LOAD} = 0.1 \mu F \mid\mid 10 \mu F; V_{ISO} = 3.3 V, see \\ \hline Figure 7- 25, Figure 7- 26 \qquad \qquad 48\% \\ \hline CMTI \qquad Common-mode transient immunity \qquad Slew Rate of GNDP versus GNDS, V_{CM} = 1200 V_{RMS} \qquad \pm 100 \qquad \pm 150 \qquad kV_{CM} = 100 V_{RMS} \\ \hline V_{ISO} = 130 mA, C_{LOAD} = 0.1 \mu F \mid\mid 10 \mu F; V_{ISO} = 3.3 V, see \\ \hline Figure 7- 25, Figure 7- 26 \qquad \qquad 48\% \\ \hline CMTI \qquad Common-mode transient immunity \qquad Slew Rate of GNDP versus GNDS, V_{CM} = 1200 V_{RMS} \qquad \pm 100 \qquad \pm 150 \qquad kV_{CM} = 100 V_{CM} = 100 V_{CM$	VISO _(LOAD)	Load regulation	SEL short to GNDS (3.3V output), I _{ISO} = 0 to 130mA,		1%	2%			
$I_{ISO} = 130$ mA, $C_{LOAD} = 0.1$ µF 10 µF; $V_{ISO} = 3.3$ V, see Figure 7- 25, Figure 7- 26 CMTI Common-mode transient immunity Slew Rate of GNDP versus GNDS, $V_{CM} = 1200$ V _{RMS} ± 100 ± 150 kV $V_{ISO} = 130$ ± 100 ± 150 kV $V_{ISO} = 130$ ± 100		Efficiency Quantity	I _{ISO} = 130 mA, C _{LOAD} = 0.1μF 10μF; V _{ISO} =5V, see		55%				
CMTI Common-mode transient immunity Slew Rate of GNDP versus GNDS, V _{CM} =1200V _{RMS} ±100 ±150 kV V _{so ripple voltage} (neak to neak) 10% to 90% load step with 5A/us slew-rate; see	EFF	Eπiciency@maximum load current	I_{ISO} = 130mA, C_{LOAD} = 0.1 μ F 10 μ F; V_{ISO} =3.3V, see		48%				
Viso ripple voltage (peak to peak) 10% to 90% load step with 5A/us slew-rate; see	CMTI	Common-mode transient immunity		±100	±150		kV/μs		
	V _{ISO} ripple v	voltage (peak to peak)	10% to 90% load step with 5A/us slew-rate; see		80	100	mV		
Transient Output Power (overload) $V_{INP} = 5V$, $V_{ISO} = 5.4V$ 1	Transient O	output Power (overload)		1			W		

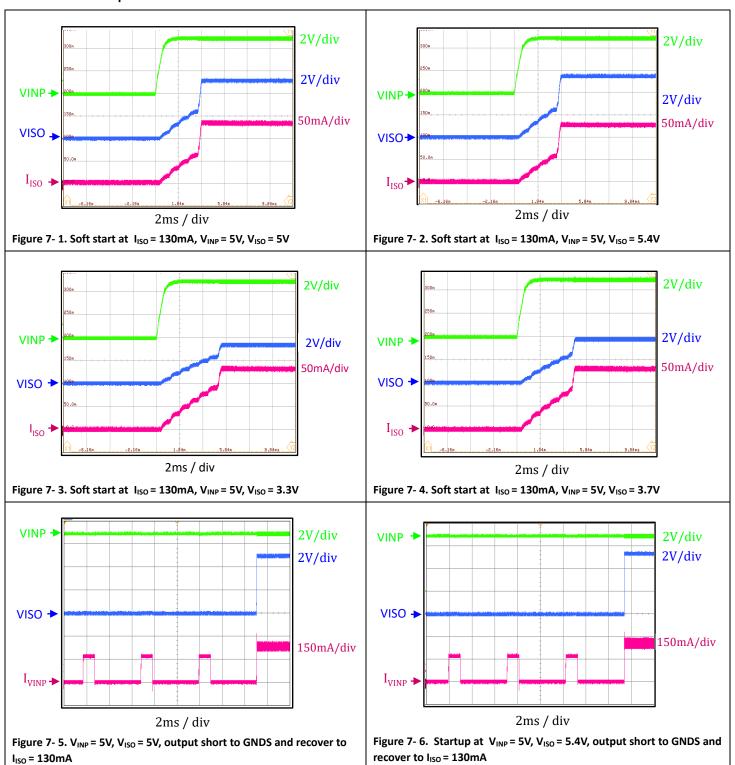
7.9 MSL

Parameters	Standard	Level			
MSL	IPC/JEDEC J-STD-020D.1	MSL 3			

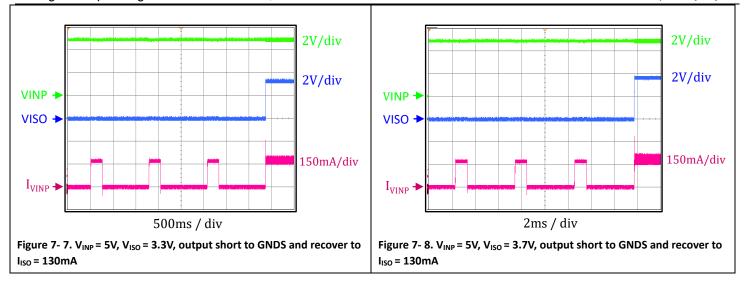
CHIPANALOG

7.10 Typical Operating Characteristics

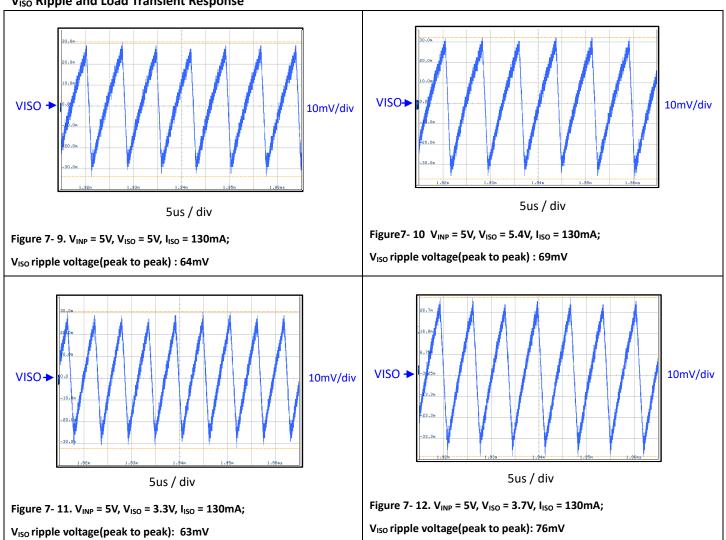
Soft-Start and Output Short-Circuit Protection



Shanghai Chipanalog Microelectronics Co., Ltd.



V_{ISO} Ripple and Load Transient Response





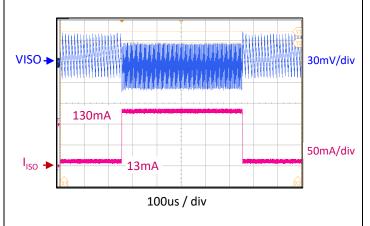


Figure 7- 13. V_{ISO} Load transient response V_{INP} = 5V, V_{ISO} = 5V, Load step: 13mA to 130mA; V_{ISO} ripple voltage(peak to peak): 16mV

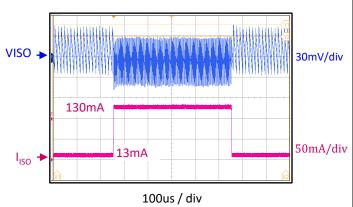


Figure 7- 14. V_{ISO} Load transient response V_{INP} = 5V, V_{ISO} = 5.4V, Load step: 13mA to 130mA; V_{ISO} ripple voltage(peak to peak): 17mV

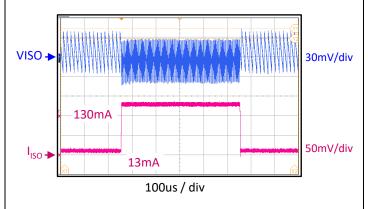


Figure 7- 15. V_{ISO} Load transient response: V_{INP} = 5V, V_{ISO} = 3.3V, Load step: 13mA to 130mA; V_{ISO} ripple voltage(peak to peak): 15mV

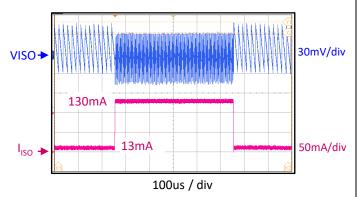


Figure 7- 16. V_{ISO} Load transient response: V_{INP} = 5V, V_{ISO} = 3.7V, Load step: 13mA to 130mA; V_{ISO} ripple voltage(peak to peak): 16mV

Load Regulation and Line Regulation

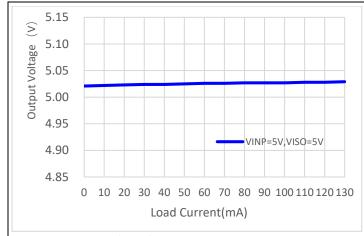


Figure 7- 17. V_{ISO} Load Regulation; V_{INP} = 5V, V_{ISO} = 5V

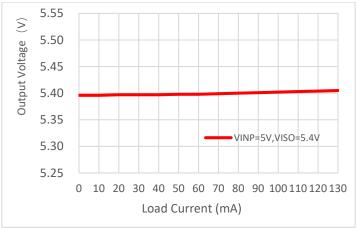
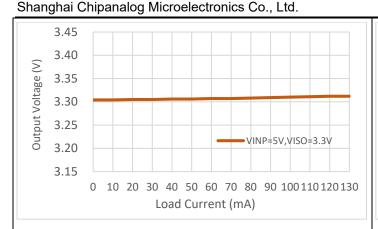


Figure 7- 18. V_{ISO} Load Regulation; V_{INP} = 5V, V_{ISO} = 5.4V





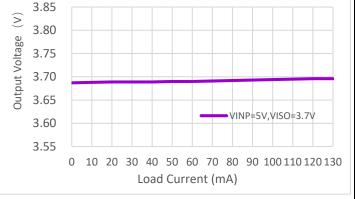
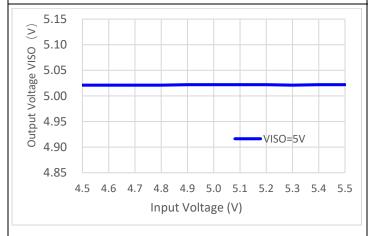


Figure 7- 19. V_{ISO} Load Regulation; V_{INP} = 5V, V_{ISO} = 3.3V

Figure 7- 20. V_{ISO} Load Regulation; V_{INP} = 5V, V_{ISO} = 3.7V



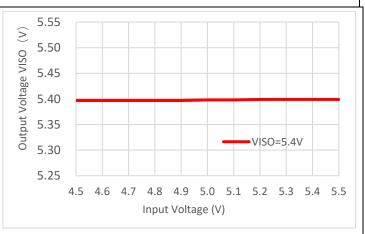
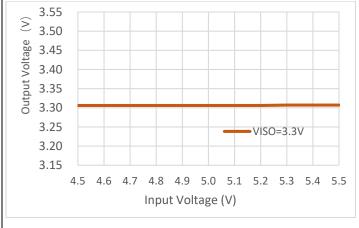


Figure 7- 21. V_{ISO} Line Regulation; V_{INP} = 4.5V to 5V, V_{ISO} = 5V

Figure 7- 22. V_{ISO} Line Regulation; V_{INP} = 4.5V to 5V, V_{ISO} = 5.4V



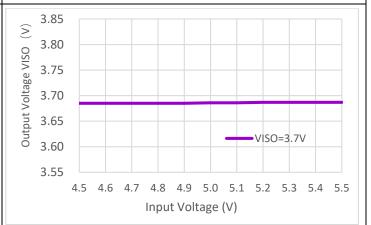


Figure 7- 23. V_{ISO} Line Regulation; V_{INP} = 4.5V to 5V, V_{ISO} = 3.3V

Figure 7- 24. V_{ISO} Line Regulation; V_{INP} = 4.5V to 5V, V_{ISO} = 3.7V

Power Supply Efficiency vs. Load Current

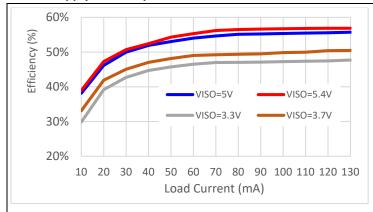


Figure 7- 25. Power Supply Efficiency vs. Load Current

 $V_{INP} = 5V$, $V_{ISO} = 5V$; $V_{INP} = 5V$, $V_{ISO} = 5.4V$;

 $V_{INP} = 5V$, $V_{ISO} = 3.3V$; $V_{INP} = 5V$, $V_{ISO} = 3.7V$

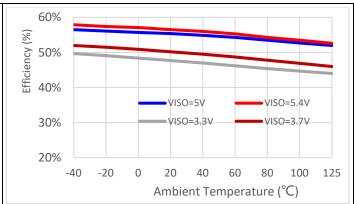


Figure 7-26. Power Supply Efficiency vs. Temperature

 $V_{INP} = 5V$, $V_{ISO} = 5V$; $V_{INP} = 5V$, $V_{ISO} = 5.4V$;

 $V_{INP} = 5V$, $V_{ISO} = 3.3V$; $V_{INP} = 5V$, $V_{ISO} = 3.7V$

Quiescent Current and Shutdown Current

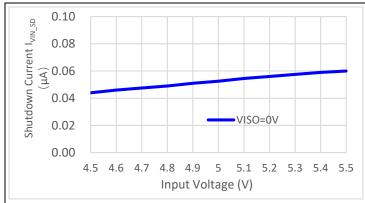


Figure 7- 27. Shutdown Current vs. Input voltage;

 V_{INP} = 4.5V to 5.5V, EN connected to GNDP

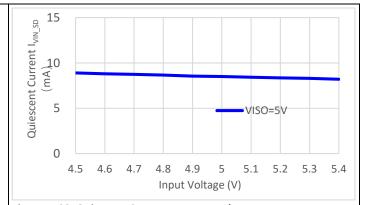


Figure 7-28. Quiescent Current vs. Input Voltage V_{INP} = 4.5V to 5.5V, V_{ISO} = 5V, EN connected to VINP

Maximum Output Current vs. Temperature

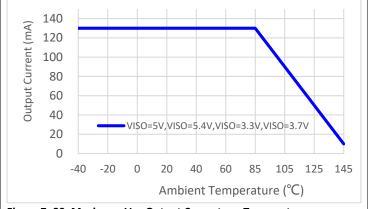


Figure 7- 29. Maximum V_{ISO} Output Current vs. Temperature,



Detailed Description 8

8.1 Overview

The CA-IS3105W is a complete isolated DC-DC converter designed to provide isolated power with up to 650mW output power across a 5kV_{RMS} isolation barrier. The device operates over 4.5V to 5.5V input voltage range and uses a proprietary control mechanisms. The input supply V_{INP} is provided to the primary power controller that switches the power stage connected to the integrated transformer. Power is transferred to the secondary side and regulated to a fixed output voltage set by the SEL pin. The soft-start feature allows to reduce input inrush current and avoid output overshoot. The device also incorporates an output enable (EN) control and undervoltage lockout function that allows the user to turn on the part at the desired input-voltage level. Figure 8-1 shows the CA-IS3105W's functional block diagrams. Connect the EN pin to VINP or force this pin high to turn on the DC-DC converter. Force this pin low to disable the device and enter low-current shutdown mode. This device offers a ready-made, reliable, easy-to-use solution and allows users save PCB space and reduce design time for the popular 5V, 3.3V power supply systems.

The device is provided with a robust overcurrent protection scheme that protects the device under overload and output short-circuit conditions. A cycle-by-cycle peak current limit turns off the switching operation and triggers a hiccup mode. Once the hiccup timeout period expires, soft-start is attempted again. Hiccup mode operation ensures low power dissipation under output short-circuit conditions.

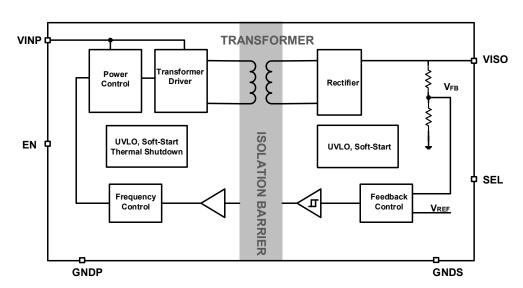


Figure 8-1. Functional Block Diagrams

8.2 **Output Voltage Selection**

At startup, the CA-IS3105W monitors the state of pin SEL after applying V_{INP} supply voltage above the UVLO rising threshold or enabling via the EN pin, to detect the desired regulation voltage level for the V_{ISO} output. After this initial monitoring, the SEL pin no longer affects the V_{ISO} output level. In order to change the output level, either the EN pin must be toggled or the V_{INP} power supply must be cycled off and back on. See Table 8-1 for the output voltage selection.

EN	SEL	VISO			
High	Sorted to VISO	5V			
High	100kΩ to VISO	5.4V			
High	Shorted to GNDS	3.3V			
High	100KΩ to GNDS	3.7V			
High	OPEN	Unsupported			
Low	X	0V			

Table 8-1. V_{ISO} Output Voltage Selection



8.3 Protection Functions

8.3.1 UVLO and Soft-Start

The CA-IS3105W has an undervoltage lockout (UVLO) on the V_{INP} power supply. Upon power-up, while the V_{INP} voltage is below the threshold voltage V_{UVLO+} (2.6V, typ.) the primary side transformer driver is disabled, and V_{ISO} output is off. The output powers up once the threshold is met. This allows the user to turn on the part at stable input-voltage level.

For many applications, it is necessary to minimize the inrush current at start-up. The CA-IS3105W built-in soft-start circuit significantly reduces the start-up current spike and output voltage overshoot. Once input power supply is applied at VINP pin, the internal soft-start circuit will control the power delivered to the output gradually increase, allowing for a graceful turn-on ramp.

8.3.2 Overcurrent Protection

The CA-IS3105W is provided with an over-current protection scheme that protects the device under overload and output short-circuit conditions. A cycle-by-cycle peak current limit turns off the switching operation and triggers a hiccup mode whenever the switch current exceeds the internal current limit. Once the hiccup timeout period expires, soft-start is attempted again. The hiccup condition is cleared when the over-current is removed.

8.3.3 Thermal Shutdown

Thermal-shutdown protection limits total power dissipation in the device. When the junction temperature of the device exceeds T_{SD} , an on-chip thermal sensor shuts down the device, allowing the device to cool. The thermal sensor turns the device on again after the junction temperature cools and junction temperature drops to normal operation temperature range of the device.

9 Applications Information

9.1 Typical Application Circuit

The CA-IS3105W is high-integration isolated power supply solution. Included in the package are the switching controller, power switches, transformer, and all support components. Only output and input bypass capacitors are needed to finish the design. For the applications with LDO post regulator, it may need a single $100k\Omega$ external resistor to set the output level to 3.7V or 5.4V, see Figure 9-1 typical application circuit.

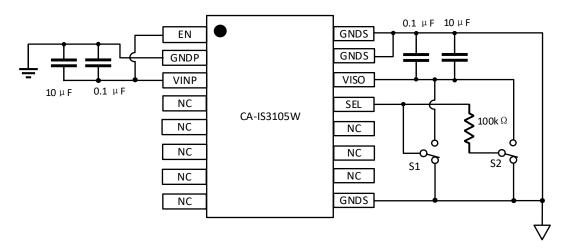


Figure 9-1. CA-IS3105W Typical Application Circuit



9.2 Input and Output Capacitors

The input capacitors (between VINP and GNDP) are required to reduce the peak current drawn from input power source and reduce the switching noise, increase efficiency. For the input capacitors, choose the ceramic capacitor because they have the lowest equivalent series resistance (ESR), smallest size, and lowest cost. For most applications, we recommend to use at least $0.1\mu F$ and $10\mu F$ ceramic capacitors with X5R or X7R temperature characteristic. When operating at a V_{INP} voltage close to the UVLO threshold, more input capacitance may be required to keep the input voltage ripple from tripping the UVLO protection.

The output capacitors between VISO and GNDS are required as well to keep the output voltage ripple small and to ensure loop stability. These bypass capacitors must have low impedance at the switching frequency. Ceramic capacitors are recommended due to their small size and low ESR. Make sure the capacitor does not degrade its capacitance significantly over temperature and DC bias. It is recommended to have at least 10µF of effective capacitance at output.

9.3 PCB Layout Guidelines

High switching frequencies and large peak currents make PCB layout a very important part of the DC-DC converter design. Good PCB design minimizes excessive electromagnetic interference (EMI) and voltage gradients in the ground plane to avoid instability and regulation errors. Even with the high level of integration, like CA-IS3105W, users may fail to achieve specified operation with a haphazard or poor layout. So careful PCB layout is critical to achieve clean and stable operation, and ensure that the grounding and heat sinking are acceptable.

Place the input capacitors, output capacitors, and the CA-IS3105W IC on the same PCB layer. Place decoupling capacitors as close as possible to the CA-IS3105W device pins, see Figure 9-2 recommended components placement for the PCB layout. The paths must be wide and short to minimize inductance, also any via holes must be avoided on these paths. Connect all of the ground (GNDP, GNDS) connections to as large a copper pour or plane area as possible for best heat-sinking. Also, we recommend grounding the NC pins to their respective ground planes to provide larger continuous ground planes and thermal mass for heat-sinking. To ensure isolation performance between the primary side and secondary side, on the top layer and bottom layer keep the space under the CA-IS3105W device free from traces, vias, and pads to maintain maximum creepage distance (≥ 8mm).

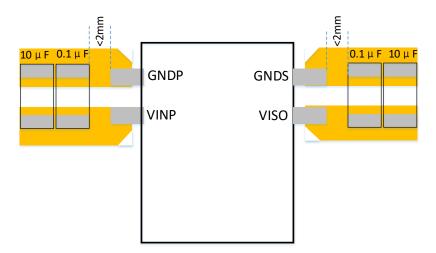
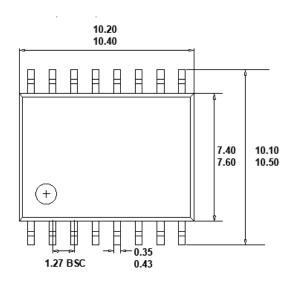


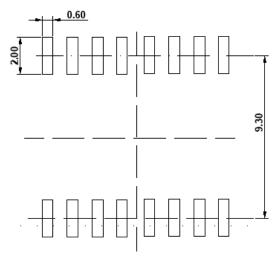
Figure 9-2. Recommended Bypass Capacitors Placement



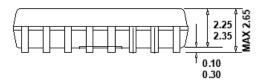
10 Package Information

The following figure illustrates the size drawing and recommended pad size of SOIC16-WB wide-body package for the CA-IS3105W isolated DC-DC converter. All dimensions are in millimeters.



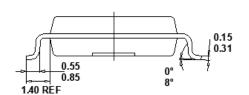


TOP VIEW



FRONT VIEW

RECOMMMENDED LAND PATTERN



LEFT SIDE VIEW



11 Soldering Temperature (reflow) Profile

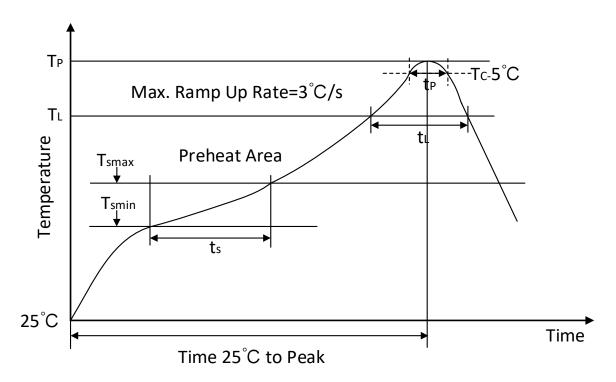


Figure 11-1 Soldering Temperature (reflow) Profile

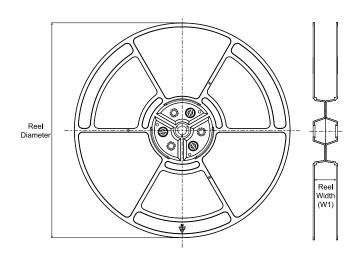
Table 11-1 Soldering Temperature Parameter

Profile Feature	Pb-Free Assembly				
Average ramp-up rate(217 °C to Peak)	3°C/second max				
Time of Preheat temp(from 150 °C to 200 °C	60-120 second				
Time to be maintained above 217 °C	60-150 second				
Peak temperature	260 +5/-0 °C				
Time within 5 °Cof actual peak temp	30 second				
Ramp-down rate	6 °C/second max.				
Time from 25°C to peak temp	8 minutes max				

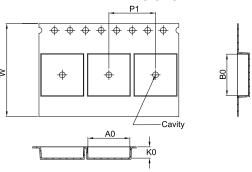


12 Tape and Reel Information

REEL DIMENSIONS

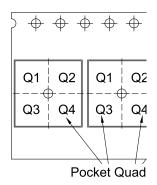


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width					
В0	Dimension designed to accommodate the component length					
K0	Dimension designed to accommodate the component					
	thickness					
W	Overall width of the carrier tape					
P1	Pitch between successive cavity centers					

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CA-IS3105W	SOIC	W	16	1000	330	16.4	10.9	10.7	3.2	12.0	16.0	Q1



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